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**PCN #189**  
**Notification Date:**  
**June 19, 2020**

## Product / Process Change Notice

**Parts Affected:**

Chip process CP371, N-channel MOSFETs, wafers and bare die.

**Extent of Change:**

The CP371 wafer process has been discontinued and is being replaced with the CP405 wafer process. See Figures 1 and 2 for details.

**Reason for Change:**

The CP371 wafer process has been replaced in order to enhance manufacturing process controls and device performance. This change will help ensure an uninterrupted supply of product.

**Effect of Change:**

The CP405 wafer process meets all electrical specifications of the individual devices listed on the following page.

**Qualification:**

P/N: CP405 Chip Process

Package: TO-220

No.	Test	Conditions (Reference standards are in bold)	Qty	Pass/Fail	Test Results
<b>1</b>	<b>Device Life Tests</b>				
A	High Temperature Gate Bias (HTGB)	T=150°C, t = 1000 hours 100% V <sub>GS</sub> Negative Bias <b>JESD22-A108</b>	77	Pass	77/77
B	High Temperature Gate Bias (HTGB)	T=150°C, t = 1000 hours 100% V <sub>GS</sub> Positive Bias <b>JESD22-A108</b>	77	Pass	77/77
C	High Temperature Reverse Bias (HTRB)	T=150°C, t = 1000 hours 100% V <sub>DS</sub> <b>JESD22-A108</b>	77	Pass	77/77

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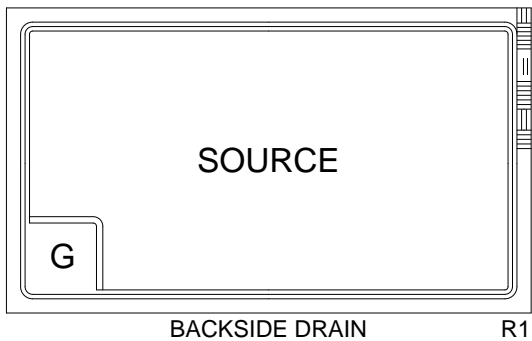
**Effective Date of Change:**

Existing inventory of chip process CP371 will be shipped until depleted.

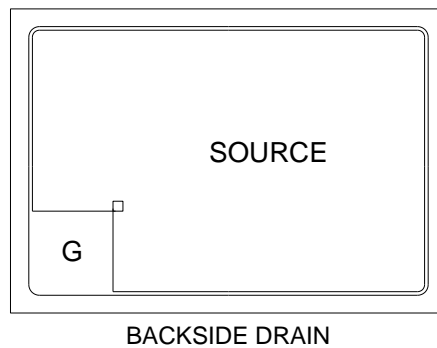
**Sample Availability:**

Please contact your salesperson or manufacturer’s representative for samples.

**Figure 1: CP371 Chip Geometry (Discontinued)**



**Figure 2: CP405 Chip Geometry**



Wafer Diameter: 8 inch  
Die Size: 55 x 32 mils  
Die Thickness: 7.5 mils  
Bond Pad Size (Gate): 7.3 x 7.3 mils  
Bond Pad Size (Source): 50 x 25 mils  
Topside Metal: Al (40,000Å)  
Backside Metal: Ti/Ni/Ag (1,000Å/3,000Å/10,000Å)

Wafer Diameter: 8 inch  
Die Size: 45.7 X 31.9 mils  
Die Thickness: 5.5 mils  
Bond Pad Size (Gate): 8.1 x 8.1 mils  
Bond Pad Size (Source): 41.9 x 28.2 mils  
Topside Metal: Al-Cu (40,000Å)  
Backside Metal: Ti/Ni/Ag (1,000Å/3,000Å/10,000Å)

**Part Numbers Affected:**

CP371-WN	CXDM4060N
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As per JEDEC standard JESD46, Customer Notification of Product/Process Changes by Solid-State Suppliers, a lack of acknowledgement of a PCN within thirty (30) days constitutes acceptance of the change.

The undersigned acknowledges and accepts Central Semiconductor's Product/Process Change Notification (PCN).

Company Name:	
Address:	
Printed Name:	
Title:	
Signature:	
Date:	